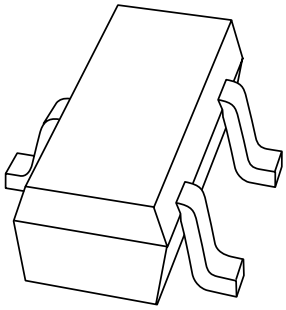
DATA SHEET



BC856T; BC857T series
PNP general purpose transistors

Product data sheet
Supersedes data of 1999 Apr 26

2000 Nov 15

PNP general purpose transistors

BC856T; BC857T series

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 65 V).

APPLICATIONS

- General purpose switching and amplification, especially in portable equipment.

DESCRIPTION

PNP transistor in an SC-75 (SOT416) plastic package.
NPN complements: BC846T; BC847T series.

MARKING

TYPE NUMBER	MARKING CODE
BC856AT	3A
BC856BT	3B
BC857AT	3E
BC857BT	3F
BC857CT	3G

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

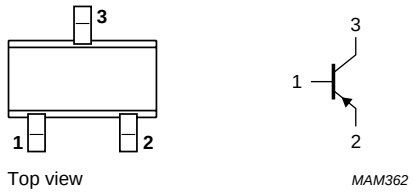


Fig.1 Simplified outline (SC-75; SOT416) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC856AT; BC856BT		–	−80	V
	BC857AT; BC857BT; BC857CT		–	−50	V
V_{CEO}	collector-emitter voltage	open base			
	BC856AT; BC856BT		–	−65	V
	BC857AT; BC857BT; BC857CT		–	−45	V
V_{EBO}	emitter-base voltage	open collector	–	−5	V
I_C	collector current (DC)		–	−100	mA
I_{CM}	peak collector current		–	−200	mA
I_{BM}	peak base current		–	−100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	150	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	in free air; note 1	833	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

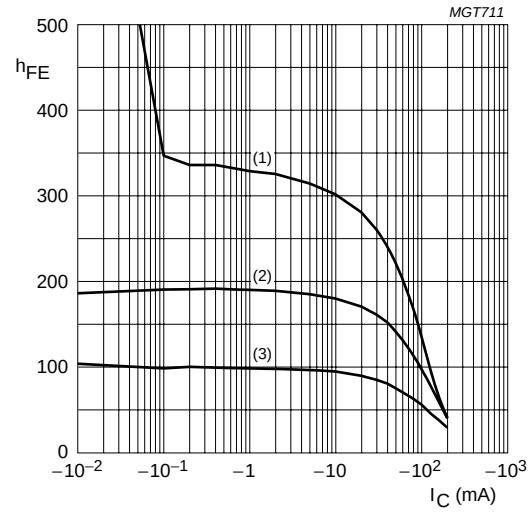
T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	V_{CB} = −30 V; I_E = 0	–	–	−15	nA
		V_{CB} = −30 V; I_E = 0; T_j = 150 °C	–	–	−5	μA
I_{EBO}	emitter cut-off current	V_{EB} = −5 V; I_C = 0	–	–	−100	nA
h_{FE}	DC current gain	V_{CE} = −5 V; I_C = −2 mA				
	BC856AT; BC857AT		125	–	250	
	BC856BT; BC857BT		220	–	475	
	BC857CT		420	–	800	
V_{CEsat}	collector-emitter saturation voltage	I_C = −10 mA; I_B = −0.5 mA	–	–	−200	mV
		I_C = −100 mA; I_B = −5 mA; note 1	–	–	−400	mV
V_{BE}	base-emitter voltage	I_C = −2 mA; V_{CE} = −5 V	−580	–	−700	mV
		I_C = −10 mA; V_{CE} = −5 V	–	–	−770	mV
C_c	collector capacitance	V_{CB} = −10 V; f = 1 MHz; I_E = i_e = 0	–	–	2.5	pF
C_e	emitter capacitance	V_{EB} = −0.5 V; f = 1 MHz; I_C = i_c = 0	–	10	–	pF
f_T	transition frequency	I_C = −10 mA; V_{CE} = −5 V; f = 100 MHz	100	–	–	MHz
F	noise figure	I_C = −200 μA; V_{CE} = −5 V; R_S = 2 kΩ; f = 1 kHz; B = 200 Hz	–	–	10	dB

Note

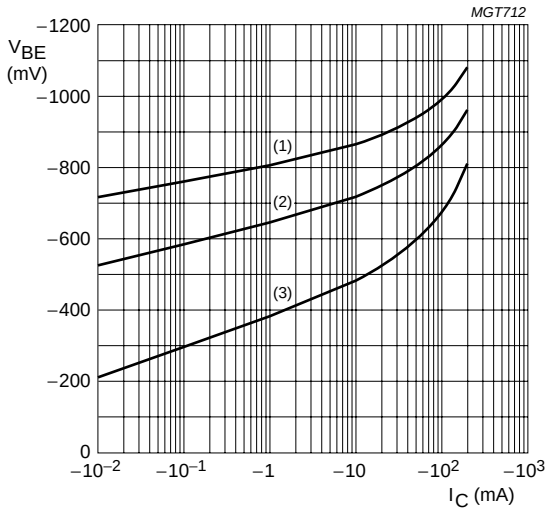
1. Pulse test: $t_p \leq 300\ \mu s$; $\delta \leq 0.02$.

GRAPHICAL INFORMATION BC857AT



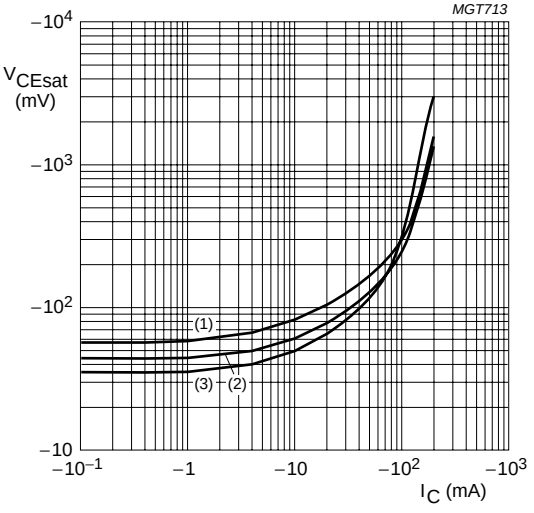
V_{CE} = −5 V.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.2 DC current gain; typical values.



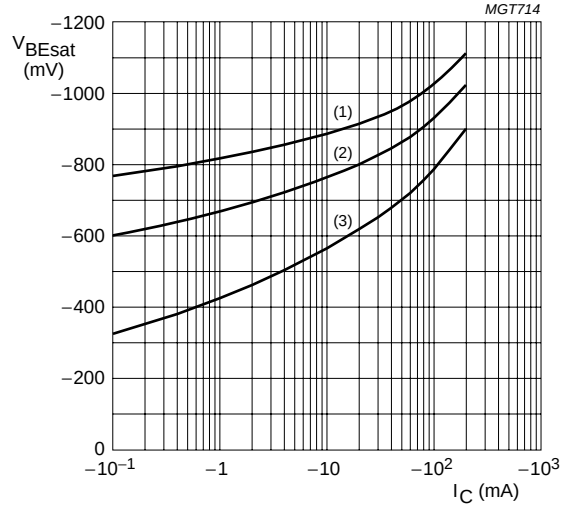
V_{CE} = −5 V.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.3 Base-emitter voltage as a function of collector current; typical values.



I_C/I_B = 20.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

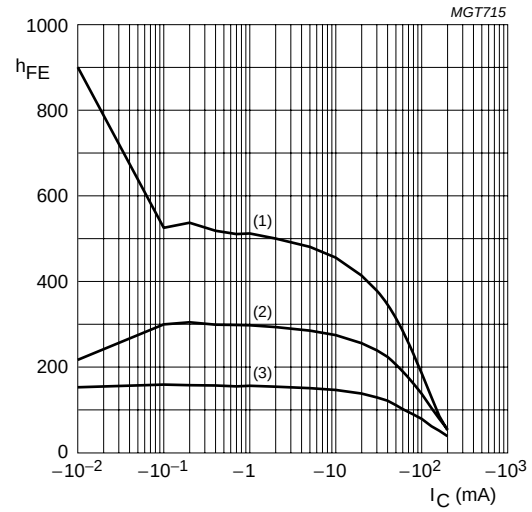
Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



I_C/I_B = 20.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

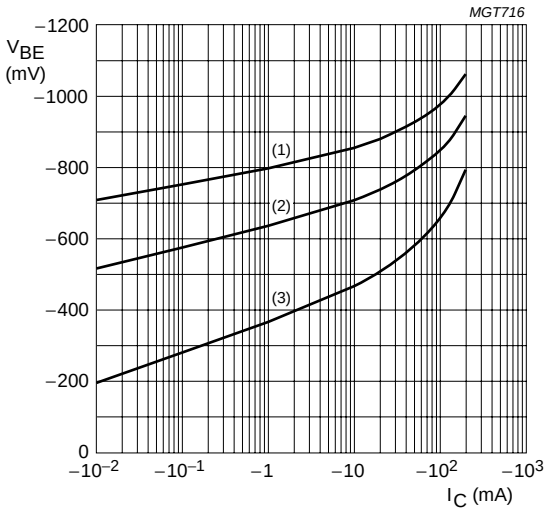
Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

GRAPHICAL INFORMATION BC857BT



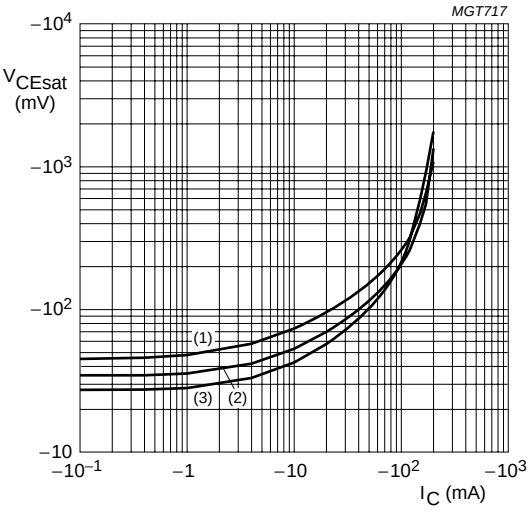
V_{CE} = −5 V.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.6 DC current gain; typical values.



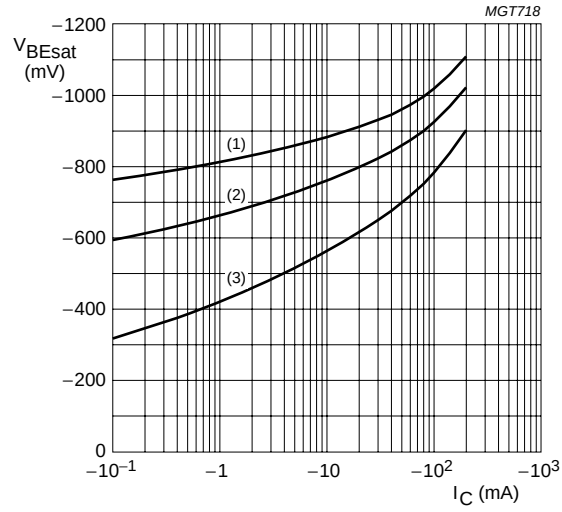
V_{CE} = −5 V.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.7 Base-emitter voltage as a function of collector current; typical values.



I_C/I_B = 20.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

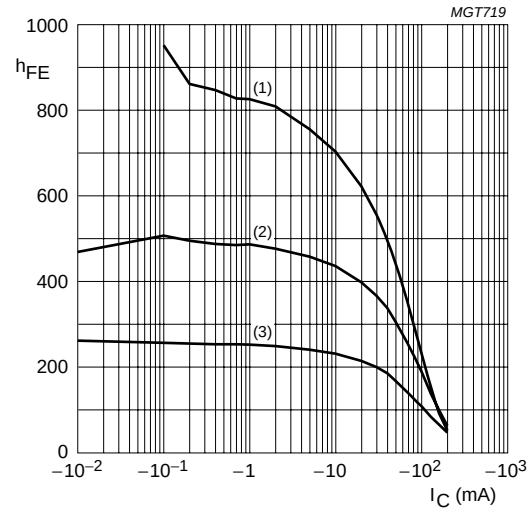
Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



I_C/I_B = 20.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

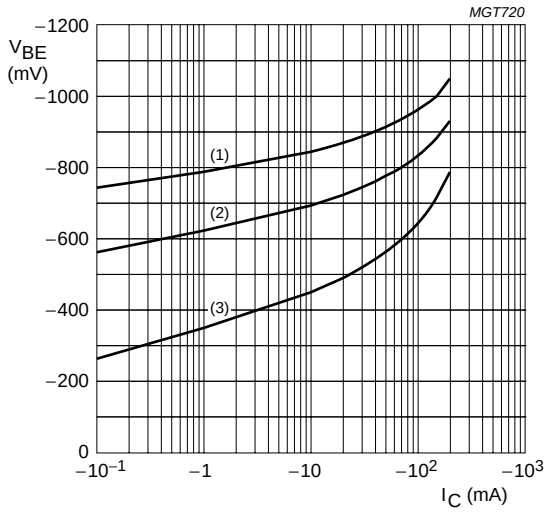
Fig.9 Base-emitter saturation voltage as a function of collector current; typical values.

GRAPHICAL INFORMATION BC857CT



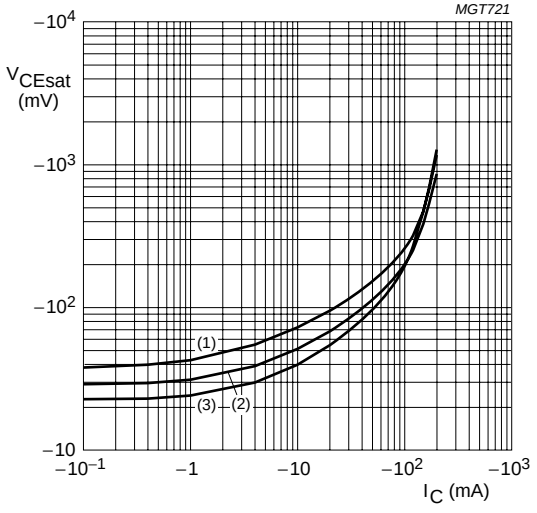
V_{CE} = −5 V.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.10 DC current gain; typical values.



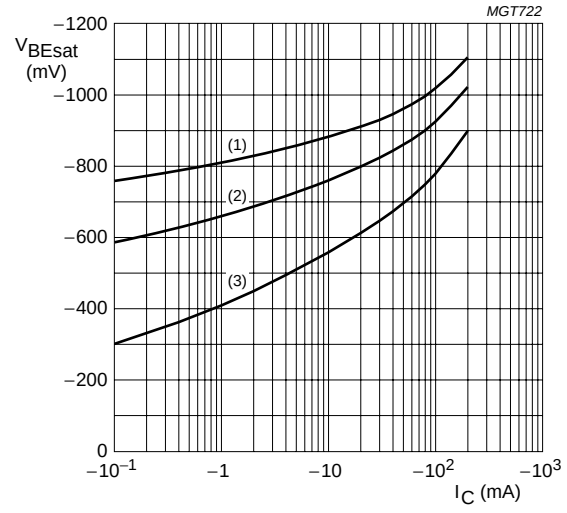
V_{CE} = −5 V.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.11 Base-emitter voltage as a function of collector current; typical values.



I_C/I_B = 20.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.12 Collector-emitter saturation voltage as a function of collector current; typical values.

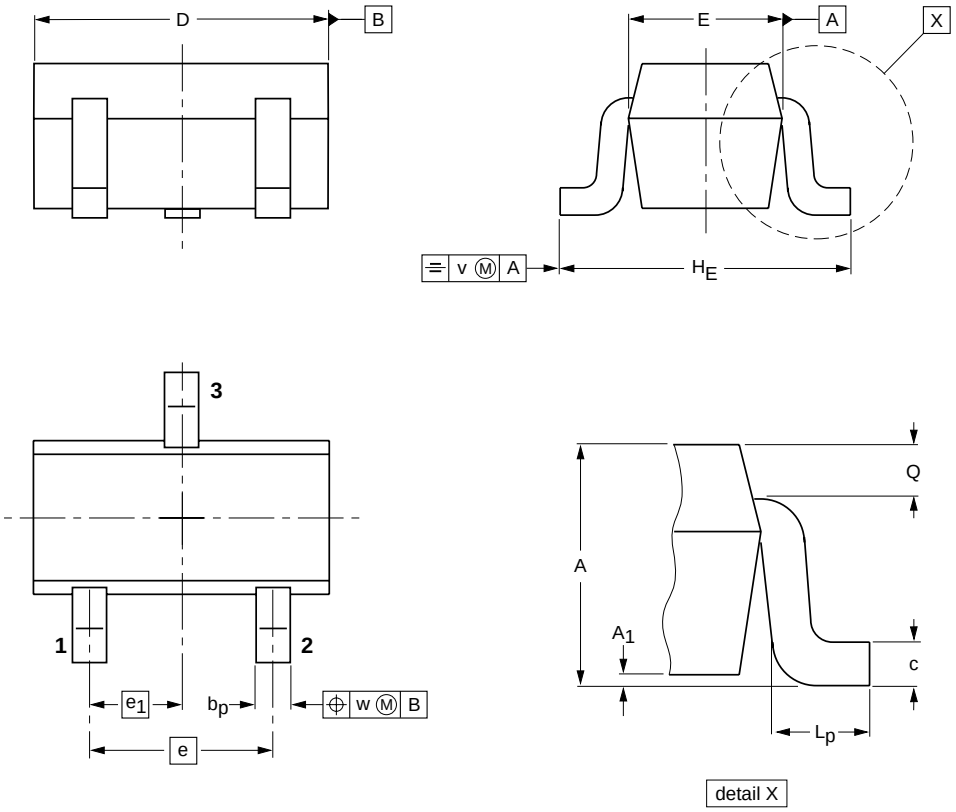


I_C/I_B = 20.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.13 Base-emitter saturation voltage as a function of collector current; typical values.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT416**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT416			SC-75			97-02-28

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

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